

# Thyristor

$$V_{RRM} = 1600V$$

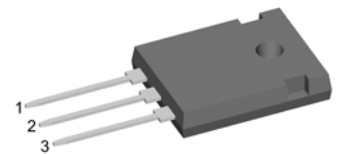
$$I_{TAV} = 40A$$

$$V_T = 1.21V$$

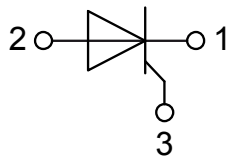
## Single Thyristor

Part number

CMA40E1600HR



Backside: isolated



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

### Applications:

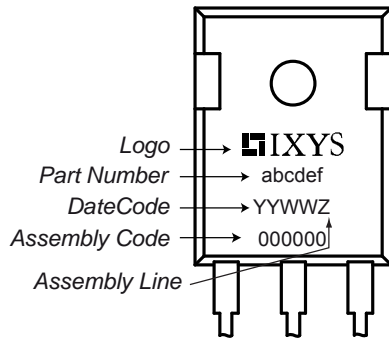
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: ISO247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

| Thyristor      |  |  |                           | Ratings |      |                   |  |
|----------------|--|--|---------------------------|---------|------|-------------------|--|
| Symbol         | Definition   | Conditions   | min.                      | typ.    | max. | Unit              |  |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$   |                           |         | 1700 | V                 |  |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}C$   |                           |         | 1600 | V                 |  |
| $I_{RD}$       | reverse current, drain current                       | $V_{R/D} = 1600 V$   | $T_{VJ} = 25^{\circ}C$    |         | 50   | $\mu A$           |  |
|                |  | $V_{R/D} = 1600 V$   | $T_{VJ} = 125^{\circ}C$   |         | 5    | mA                |  |
| $V_T$          | forward voltage drop                                 | $I_T = 40 A$   | $T_{VJ} = 25^{\circ}C$    |         | 1.23 | V                 |  |
|                |  |  |                           |         | 1.52 | V                 |  |
|                |  | $I_T = 40 A$   | $T_{VJ} = 125^{\circ}C$   |         | 1.21 | V                 |  |
|                |  |  |                           |         | 1.59 | V                 |  |
| $I_{TAV}$      | average forward current                              | $T_C = 90^{\circ}C$  | $T_{VJ} = 150^{\circ}C$   |         | 40   | A                 |  |
| $I_{T(RMS)}$   | RMS forward current                                  | 180° sine  |                           |         | 63   | A                 |  |
| $V_{T0}$       | threshold voltage                                    | } for power loss calculation only  | $T_{VJ} = 150^{\circ}C$   |         | 0.81 | V                 |  |
| $r_T$          | slope resistance                                     |  |                           |         | 9.8  | m $\Omega$        |  |
| $R_{thJC}$     | thermal resistance junction to case                  |  |                           |         | 0.8  | K/W               |  |
| $R_{thCH}$     | thermal resistance case to heatsink                  |  |                           | 0.25    |      | K/W               |  |
| $P_{tot}$      | total power dissipation                              |  | $T_C = 25^{\circ}C$       |         | 155  | W                 |  |
| $I_{TSM}$      | max. forward surge current                           | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 45^{\circ}C$    |         | 550  | A                 |  |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |         | 595  | A                 |  |
|                |  | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 150^{\circ}C$   |         | 470  | A                 |  |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |         | 505  | A                 |  |
| $I^2t$         | value for fusing                                     | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 45^{\circ}C$    |         | 1.52 | kA <sup>2</sup> s |  |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |         | 1.48 | kA <sup>2</sup> s |  |
|                |  | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 150^{\circ}C$   |         | 1.11 | kA <sup>2</sup> s |  |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |         | 1.06 | kA <sup>2</sup> s |  |
| $C_J$          | junction capacitance                                 | $V_R = 400 V$ f = 1 MHz  | $T_{VJ} = 25^{\circ}C$    |         | 26   | pF                |  |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30 \mu s$   | $T_C = 150^{\circ}C$      |         | 10   | W                 |  |
|                |  | $t_p = 300 \mu s$  |                           |         | 5    | W                 |  |
| $P_{GAV}$      | average gate power dissipation                       |  |                           |         | 0.5  | W                 |  |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 150^{\circ}C$ ; f = 50 Hz  | repetitive, $I_T = 120 A$ |         | 150  | A/ $\mu s$        |  |
|                |  | $t_p = 200 \mu s$ ; $di_G/dt = 0.3 A/\mu s$ ;<br>$I_G = 0.3 A$ ; $V_D = \frac{2}{3} V_{DRM}$ | non-repet., $I_T = 40 A$  |         | 500  | A/ $\mu s$        |  |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V_D = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)            | $T_{VJ} = 150^{\circ}C$   |         | 1000 | V/ $\mu s$        |  |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$    |         | 1.5  | V                 |  |
|                |  |  | $T_{VJ} = -40^{\circ}C$   |         | 1.6  | V                 |  |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$    |         | 50   | mA                |  |
|                |  |  | $T_{VJ} = -40^{\circ}C$   |         | 80   | mA                |  |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$  | $T_{VJ} = 140^{\circ}C$   |         | 0.2  | V                 |  |
| $I_{GD}$       | gate non-trigger current                             |  |                           |         | 5    | mA                |  |
| $I_L$          | latching current                                     | $t_p = 10 \mu s$   | $T_{VJ} = 25^{\circ}C$    |         | 125  | mA                |  |
|                |  | $I_G = 0.3 A$ ; $di_G/dt = 0.3 A/\mu s$  |                           |         |      |                   |  |
| $I_H$          | holding current                                      | $V_D = 6 V$ $R_{GK} = \infty$  | $T_{VJ} = 25^{\circ}C$    |         | 100  | mA                |  |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$  | $T_{VJ} = 25^{\circ}C$    |         | 2    | $\mu s$           |  |
|                |  | $I_G = 0.3 A$ ; $di_G/dt = 0.3 A/\mu s$  |                           |         |      |                   |  |
| $t_q$          | turn-off time  | $V_R = 100 V$ ; $I_T = 40 A$ ; $V_D = \frac{2}{3} V_{DRM}$                                   | $T_{VJ} = 150^{\circ}C$   |         | 150  | $\mu s$           |  |
|                |  | $di/dt = 10 A/\mu s$ ; $dv/dt = 20 V/\mu s$ ; $t_p = 200 \mu s$                              |                           |         |      |                   |  |

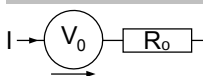
| Package ISO247 |  |                      | Ratings |      |      |      |
|----------------|--|----------------------|---------|------|------|------|
| Symbol         | Definition   | Conditions           | min.    | typ. | max. | Unit |
| $I_{RMS}$      | RMS current  | per terminal         |         |      | 70   | A    |
| $T_{VJ}$       | virtual junction temperature                                 |                      | -40     |      | 150  | °C   |
| $T_{op}$       | operation temperature  |                      | -40     |      | 125  | °C   |
| $T_{stg}$      | storage temperature  |                      | -40     |      | 150  | °C   |
| <b>Weight</b>  |  |                      |         | 6    |      | g    |
| $M_D$          | mounting torque  |                      | 0.8     |      | 1.2  | Nm   |
| $F_C$          | mounting force with clip                                     |                      | 20      |      | 120  | N    |
| $d_{Spp/App}$  | creepage distance on surface   striking distance through air | terminal to terminal | 2.7     |      |      | mm   |
| $d_{Spb/Apb}$  |  | terminal to backside | 4.1     |      |      | mm   |
| $V_{ISOL}$     | isolation voltage  | t = 1 second         | 3600    |      |      | V    |
|                |  | t = 1 minute         | 3000    |      |      | V    |

**Product Marking**

**Part description**

C = Thyristor (SCR)  
 M = Thyristor  
 A = (up to 1800V)  
 40 = Current Rating [A]  
 E = Single Thyristor  
 1600 = Reverse Voltage [V]  
 HR = ISO247 (3)

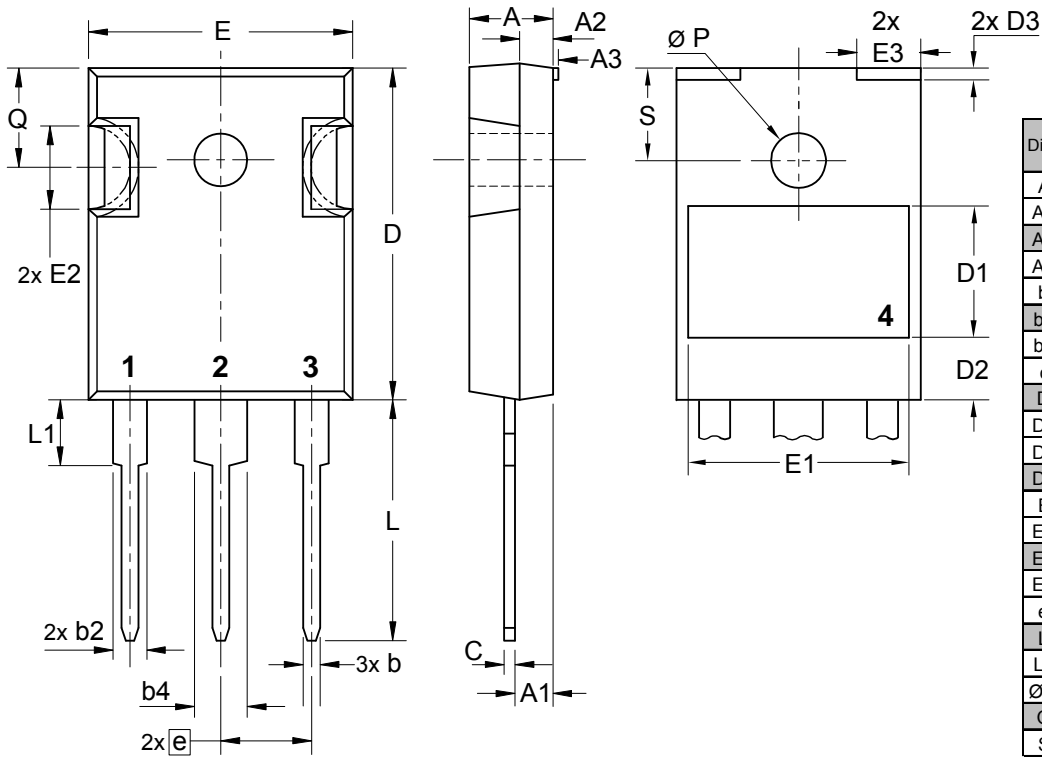
| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | CMA40E1600HR    | CMA40E1600HR       | Tuibe         | 30       | 515435   |

| Similar Part | Package    | Voltage class |
|--------------|------------|---------------|
| CLA40E1200HR | ISO247 (3) | 1200          |

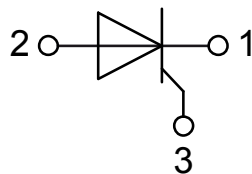
**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 150\text{ }^{\circ}\text{C}$ 

**Thyristor**

|             |                    |      |    |
|-------------|--------------------|------|----|
| $V_{0\max}$ | threshold voltage  | 0.81 | V  |
| $R_{0\max}$ | slope resistance * | 7.2  | mΩ |

## Outlines ISO247



| Dim.            | Millimeter |       | Inches     |       |
|-----------------|------------|-------|------------|-------|
|                 | min        | max   | min        | max   |
| A               | 4.70       | 5.30  | 0.185      | 0.209 |
| A1              | 2.21       | 2.59  | 0.087      | 0.102 |
| A2              | 1.50       | 2.49  | 0.059      | 0.098 |
| A3              | typ. 0.05  |       | typ. 0.002 |       |
| b               | 0.99       | 1.40  | 0.039      | 0.055 |
| b2              | 1.65       | 2.39  | 0.065      | 0.094 |
| b4              | 2.59       | 3.43  | 0.102      | 0.135 |
| c               | 0.38       | 0.89  | 0.015      | 0.035 |
| D               | 20.79      | 21.45 | 0.819      | 0.844 |
| D1              | typ. 8.90  |       | typ. 0.350 |       |
| D2              | typ. 2.90  |       | typ. 0.114 |       |
| D3              | typ. 1.00  |       | typ. 0.039 |       |
| E               | 15.49      | 16.24 | 0.610      | 0.639 |
| E1              | typ. 13.45 |       | typ. 0.530 |       |
| E2              | 4.31       | 5.48  | 0.170      | 0.216 |
| E3              | typ. 4.00  |       | typ. 0.157 |       |
| e               | 5.46 BSC   |       | 0.215 BSC  |       |
| L               | 19.80      | 20.30 | 0.780      | 0.799 |
| L1              | -          | 4.49  | -          | 0.177 |
| $\varnothing P$ | 3.55       | 3.65  | 0.140      | 0.144 |
| Q               | 5.38       | 6.19  | 0.212      | 0.244 |
| S               | 6.14 BSC   |       | 0.242 BSC  |       |



## Thyristor

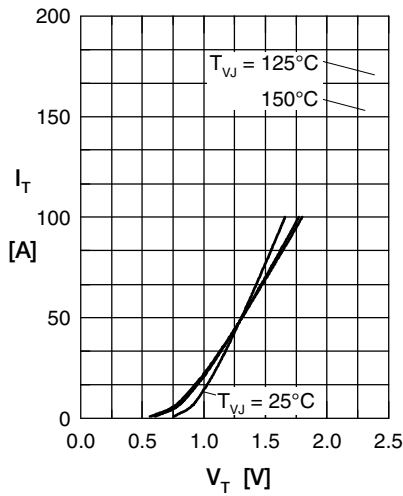


Fig. 1 Forward characteristics

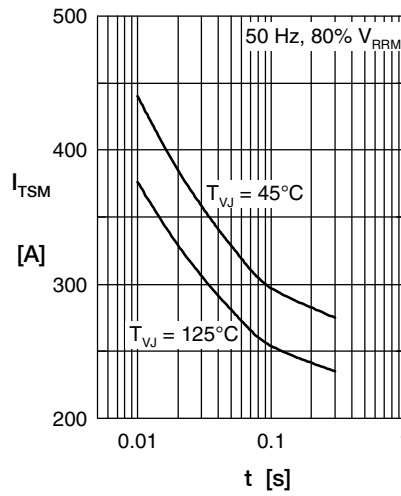


Fig. 2 Surge overload current  $I_{TSM}$ : crest value,  $t$ : duration

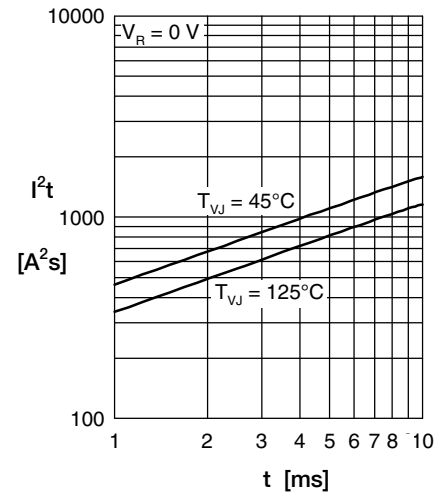


Fig. 3  $I^2t$  versus time (1-10 s)

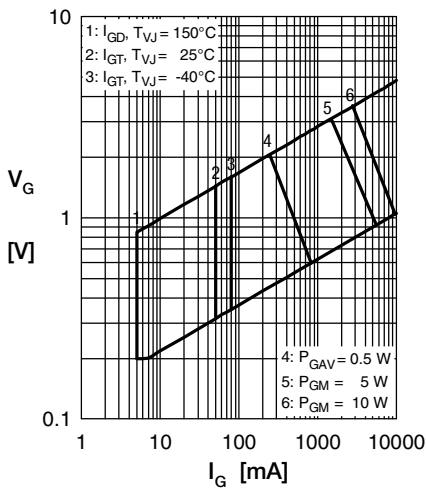


Fig. 4 Gate voltage & gate current

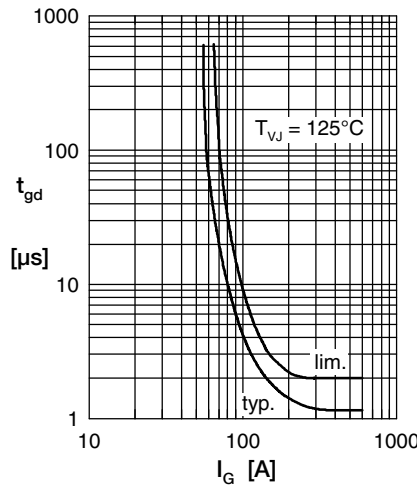


Fig. 5 Gate controlled delay time  $t_{gd}$

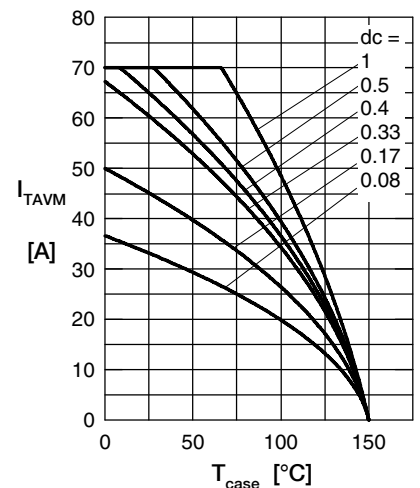


Fig. 6 Max. forward current at case temperature

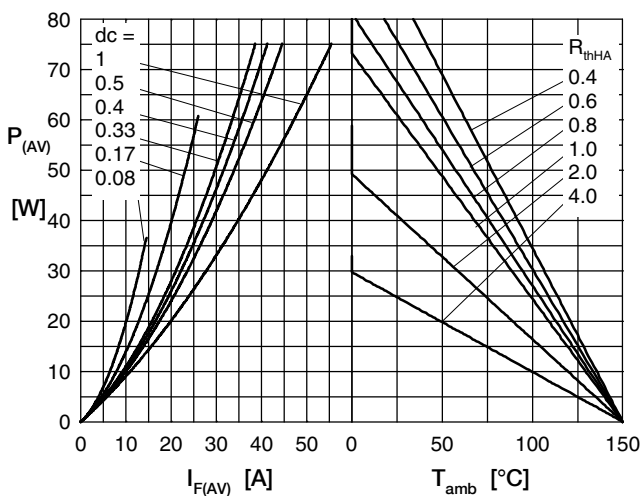


Fig. 7a Power dissipation versus direct output current  
Fig. 7b and ambient temperature

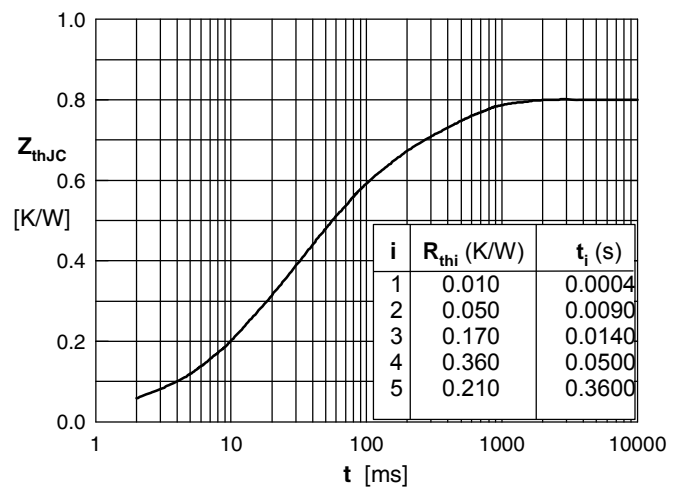


Fig. 7 Transient thermal impedance junction to case